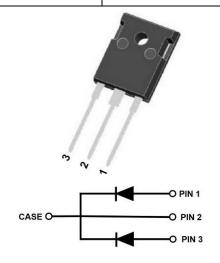


Silicon Carbide Schottky Diode

V_{RRM}	1200V
I _{F (135°C)}	42A ⁽²⁾
Q _C	186nC ⁽²⁾



Features

- Positive temperature coefficient
- Temperature-independent switching
- Maximum working temperature at 175 °C
- Unipolar devices and zero reverse recovery current
- Zero forward recovery current
- Essentially no switching losses
- Reduction of heat sink requirements
- High-frequency operation
- Reduction of EMI

Typical Applications

Typical applications are in power factor correction(PFC), solar inverter, uninterruptible power supply, motor drives, photovoltaic inverter, electric car and charger.

Mechanical Data

• Package: TO-247AB

• Terminals: Tin plated leads

• Polarity: As marked

■Maximum Ratings (T_C=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	VALUE
Device marking code			D112040NCTYG5
Reverse voltage (Repetitive peak) @ T _j =25°C	V_{RRM}	V	1200
Reverse voltage (Surge peak) @ T _j =25°C	V_{RSM}	V	1200
Reverse voltage (DC) @ T _j =25°C	V _{DC}	V	1200
Continuous forward current @ T _C =25°C			45/90
Continuous forward current @ T _C =135°C	I _F	Α	21/42
Continuous forward current @ T _C =140°C			20/40
Non-repetitive peak forward surge current @ T _C =25°C, tp=10ms, Half Sine Wave	I _{FSM}	Α	180 ⁽¹⁾
Power Dissipation@ T _C =25°C	Ртот	W	187/365
Power Dissipation@ T _C =110°C	Гтот		81/158
i²t Value@ T _C =25°C ,tp=10ms	∫i²dt	A ² S	162 ⁽¹⁾
Operating junction and Storage temperature range	T_{j} , T_{stg}	°C	-55 to +175

⁽¹⁾ Per Leg, (2) Per Device

■Electrical Characteristics (Per Leg)

PARAMETER	SYMBOL	UNIT	TEST CONDITIONS	Тур.	Max.
Forward voltage drop	V _F	V	I _F =20A, T _j =25°C	1.48	1.70
			I _F =20A, T _j =175°C	2.2	-
Reverse current	I _R	μA	V _R =1200V, T _j =25°C	0.5	25
			V _R =1200V, T _j =175°C	30	-
Total capacitive charge	Qc	nC	$\begin{array}{c} V_R {=} 800 V, T_j {=} 25^{\circ} C \; , \\ Q_C {=} \int_0^{VR} C(V) dV \end{array} \label{eq:VR}$	93	-
Total capacitance	С	pF	V _R =0V, f=1MHZ	1265	-
			V _R =400V, f=1MHZ	87	-
			V _R =800V, f=1MHZ	67	-
Capacitance stored energy	Ec	μJ	V _R =800V	26.5	-

■Thermal Characteristics (Ta=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	VALUE
Thermal resistance	$R_{\theta J-C}$	°C W	0.80 ⁽¹⁾ 0.41 ⁽²⁾

⁽¹⁾ Per Leg, ⁽²⁾ Per Device

■Typical Characteristics (Per Leg)

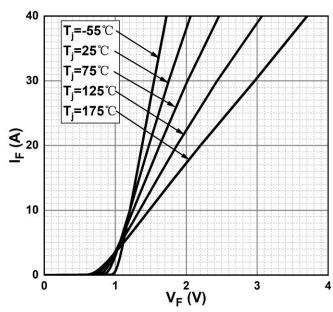


Figure 1. Forward Characteristics

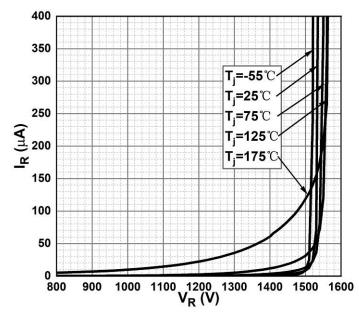
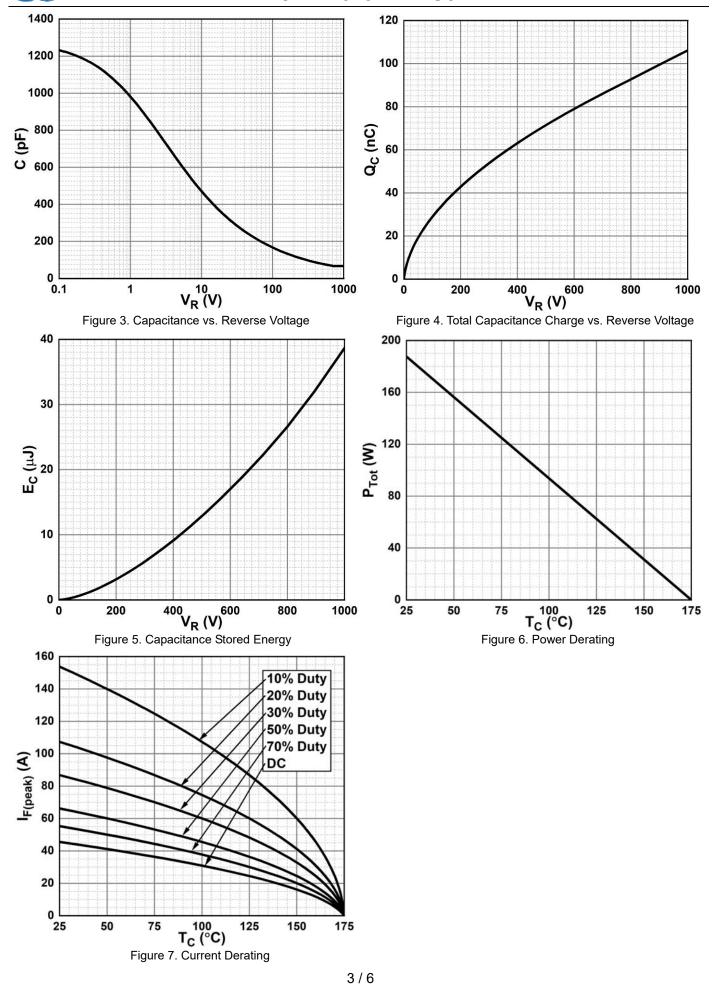


Figure 2. Reverse Characteristics





■Typical Characteristics (Device)

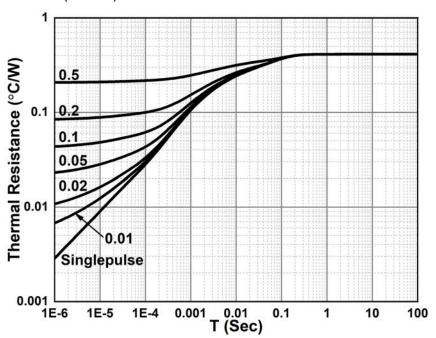


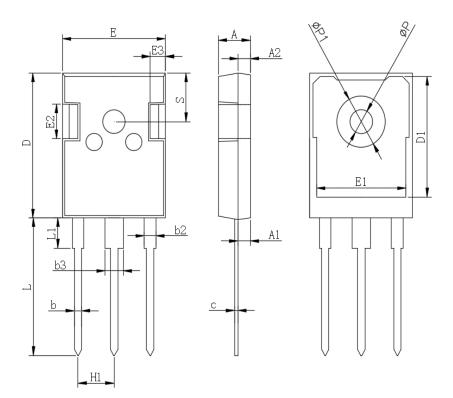
Figure 8. Transient Thermal Impedance





■Outline Dimensions

TO-247AB



TO-247AB				
Dim	Min	Max		
Α	4.80	5.20		
A1	2.21	2.61		
A2	1.85	2.15		
b	1.0	1.4		
b2	1.91	2.21		
С	0.5	0.7		
D	20.70	21.30		
D1	16.25	16.85		
E	15.50	16.10		
E1	13.0	13.6		
E2	4.80	5.20		
E3	2.30	2.70		
L	19.62	20.22		
L1	-	4.30		
ФР	3.40	3.80		
ФР1	-	7.30		
S	6.15TYP			
H1	5.44TYP			
b3	2.80	3.20		



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